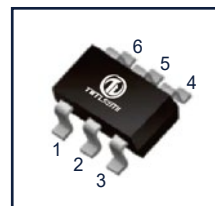
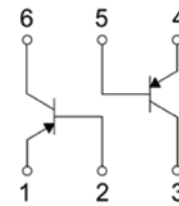


Features

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors



SOT-363



Equivalent Circuit

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-50	V
V_{CE0}	Collector-Emitter Voltage	-45	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.2	A
P_C	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	417	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CB0}$	Collector-base breakdown voltage	$I_C=-10\mu\text{A}, I_E=0$	-50			V
$V_{(BR)CE0}$	Collector-emitter breakdown voltage	$I_C=-10\text{mA}, I_B=0$	-45			V
$V_{(BR)EB0}$	Emitter-base breakdown voltage	$I_E=-10\mu\text{A}, I_C=0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB}=-30\text{V}, I_E=0$			-15	nA
h_{FE}	DC current gain	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	200		450	
$V_{CE(sat)(1)}$	Collector-emitter saturation voltage	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$			-0.3	V
$V_{CE(sat)(2)}$		$I_C=-100\text{mA}, I_B=-5\text{mA}$			-0.65	V
$V_{BE(sat)(1)}$	Base-emitter saturation voltage	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	-0.6		-0.75	V
$V_{BE(sat)(2)}$		$V_{CE}=-5\text{V}, I_C=-10\text{mA}$			-0.82	V
f_T	Transition frequency	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$		200		MHz
C_{ob}	Base-emitter saturation voltage	$V_{CB}=-10\text{V}, I_E=0\text{A}, f=1\text{MHz}$		3.5		pF
NF	Noise figure	$V_{CE}=-5\text{V}, I_C=-0.2\text{mA}, f=1\text{kHz}, R_S=2\text{K}\Omega, BW=200\text{Hz}$		2.5		dB

Ordering information

Product ID	Pack	Naming rule	Marking	$h_{FE}(1)$	Qty(PCS)
BC857S	SOT-363	BC857S 产品名称 product name	3C	200-450	3000
			3F		



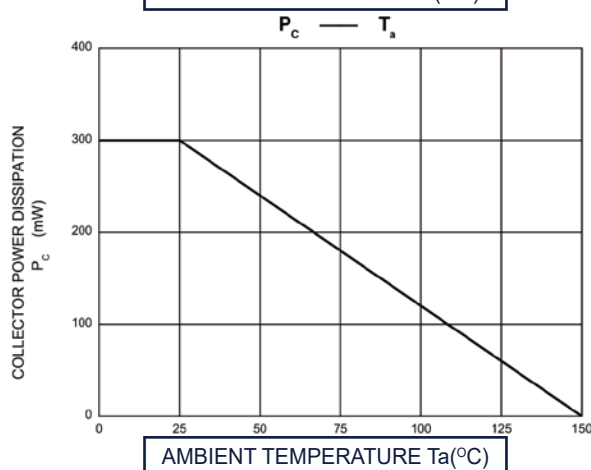
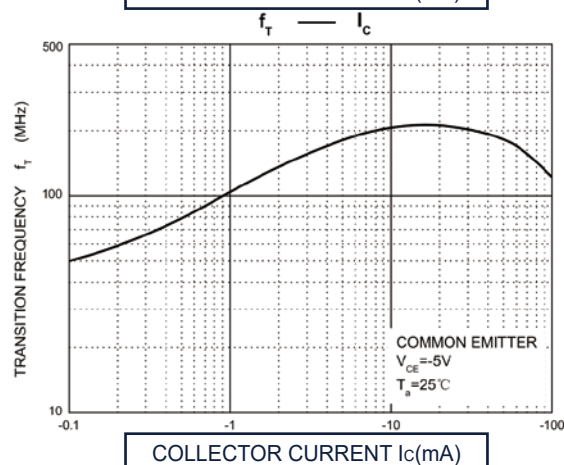
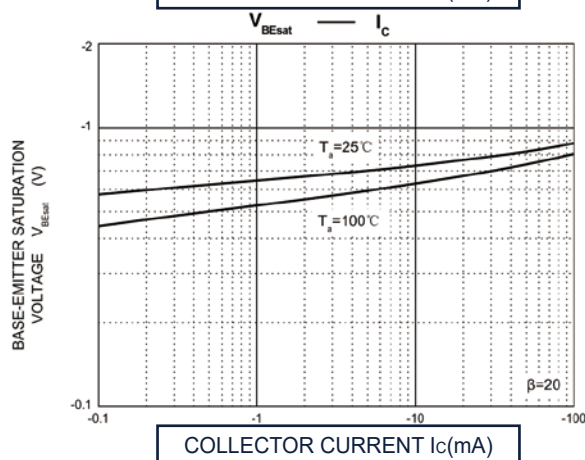
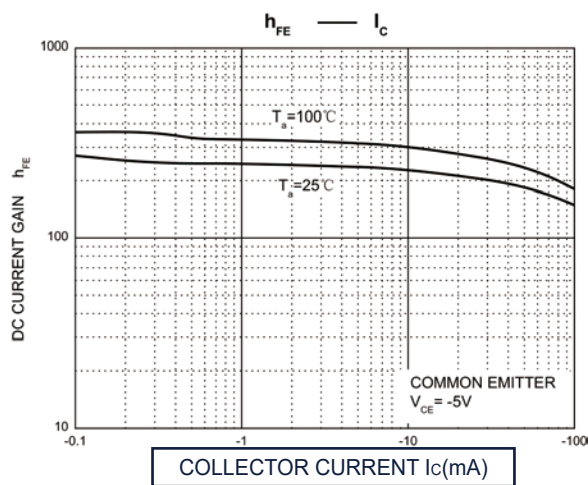
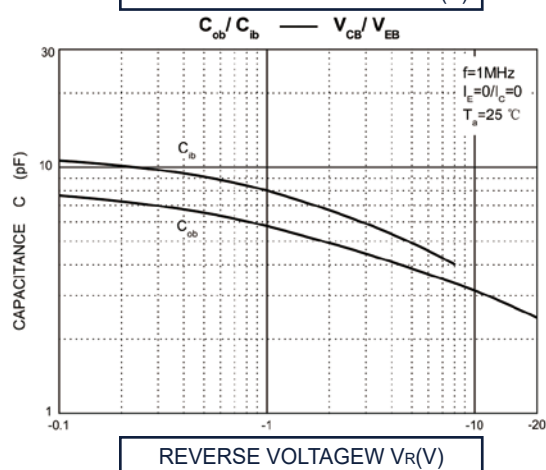
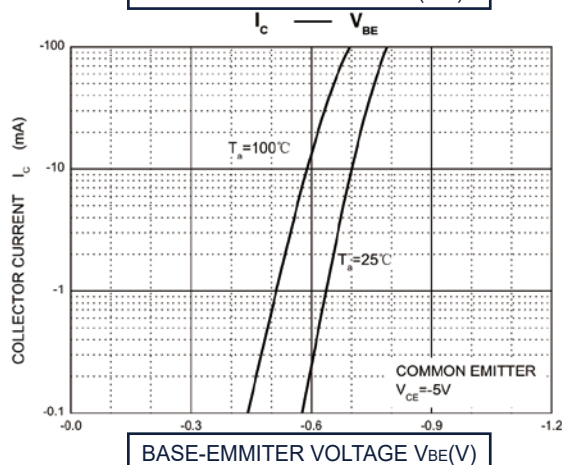
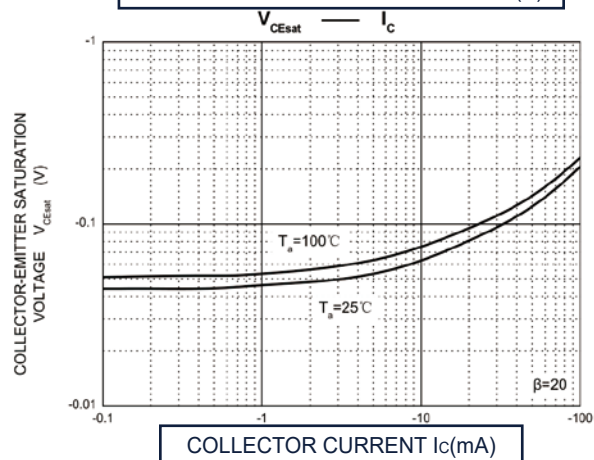
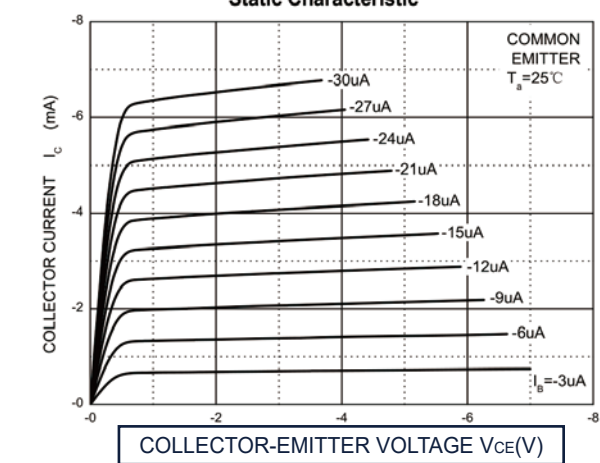
TWTLSEMI

TL-BC857S

SOT-363 DUAL TRANSISTOR (PNP+PNP)

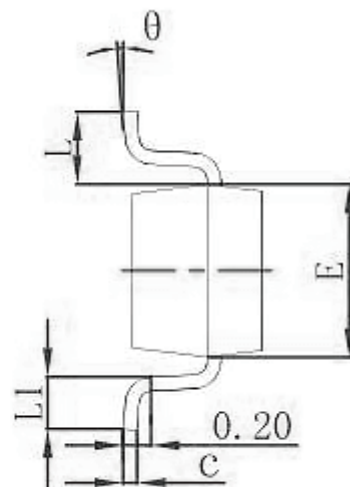
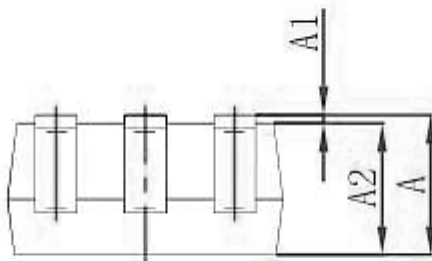
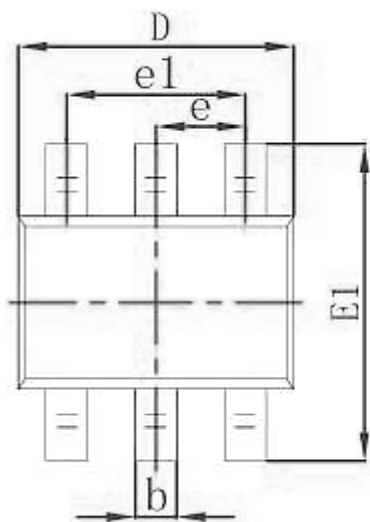
Typical Characteristics

Static Characteristic





SOT-363 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°